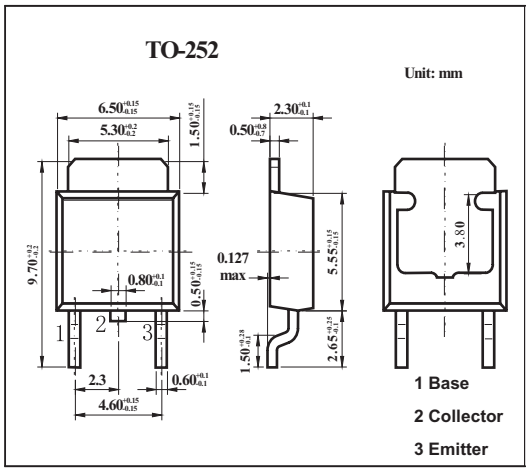
NPN Silicon Epitaxial Transistor

2SC2983



Features

- High Transiton Frequency: Ft=100MHz(TYP.)

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	160	V
Collector to emitter voltage	V_{CEO}	160	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	1.5	A
Base Current	I_B	0.3	A
Total Power dissipation Ta = 25℃	P_C	1	W
T_C = 25℃		15	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cutoff current	I_{CBO}	V_{CB}=160V,I_E=0			1	μA
emitter cutoff current	I_{EBO}	V_{EB}=5V,I_C=0			1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	160			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA,I_C=0	5			V
DC current Gain	h_{FE}	V_{CE}=5V,I_C=100mA	70		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA,I_B=50mA			1.5	V
Base- Emitter Voltage	V_{BE}	V_{CE}=5V,I_C=500mA			1	V
Transition Frequency	fT	V_{CE}=10V,I_C=100mA		100		MHz
Collector Output Capacitance	cob	V_{CB}=10V.I_E=0,f=1MHz		25		pF

h_{FE} Classification

Marking	O	Y
hFE	70 to 140	120 to 240